

Silicon NPN Power Transistors

2SD1197

DESCRIPTION

- With TO-3PN package
- High DC current gain.
- Large current capacity and wide ASO.
- Low saturation voltage
- DARLINGTON
- Complement to type 2SB887

APPLICATIONS

- Motor drivers, printer hammer drivers, relay drivers, voltage regulator control.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

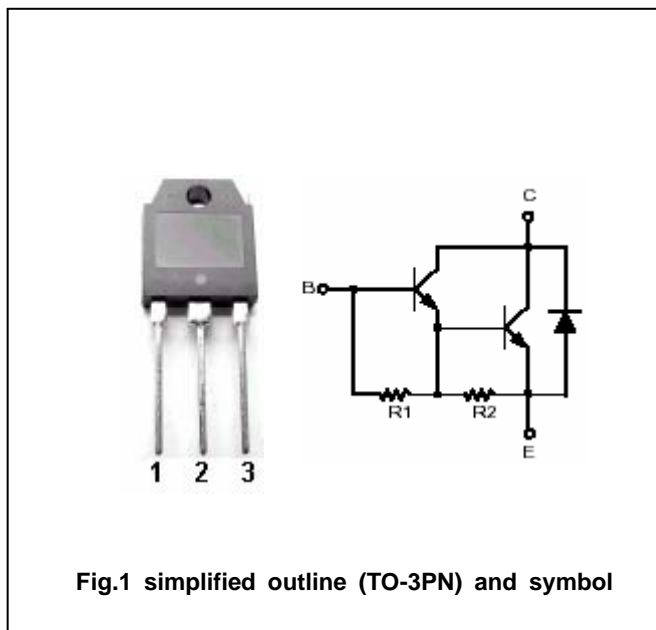


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	110	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		10	A
I_{CP}	Collector current (Pulse)		15	A
P_C	Collector power dissipation	$T_C=25$	70	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; R _{BE} =∞	100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =5mA ; I _E =0	110			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =10mA		0.9	1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A ; I _B =10mA			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =80V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			3.0	mA
h _{FE}	DC current gain	I _C =5A ; V _{CE} =3V	1500	4000		
f _T	Transition frequency	I _C =5A ; V _{CE} =5V		20		MHz

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PACKAGE OUTLINE

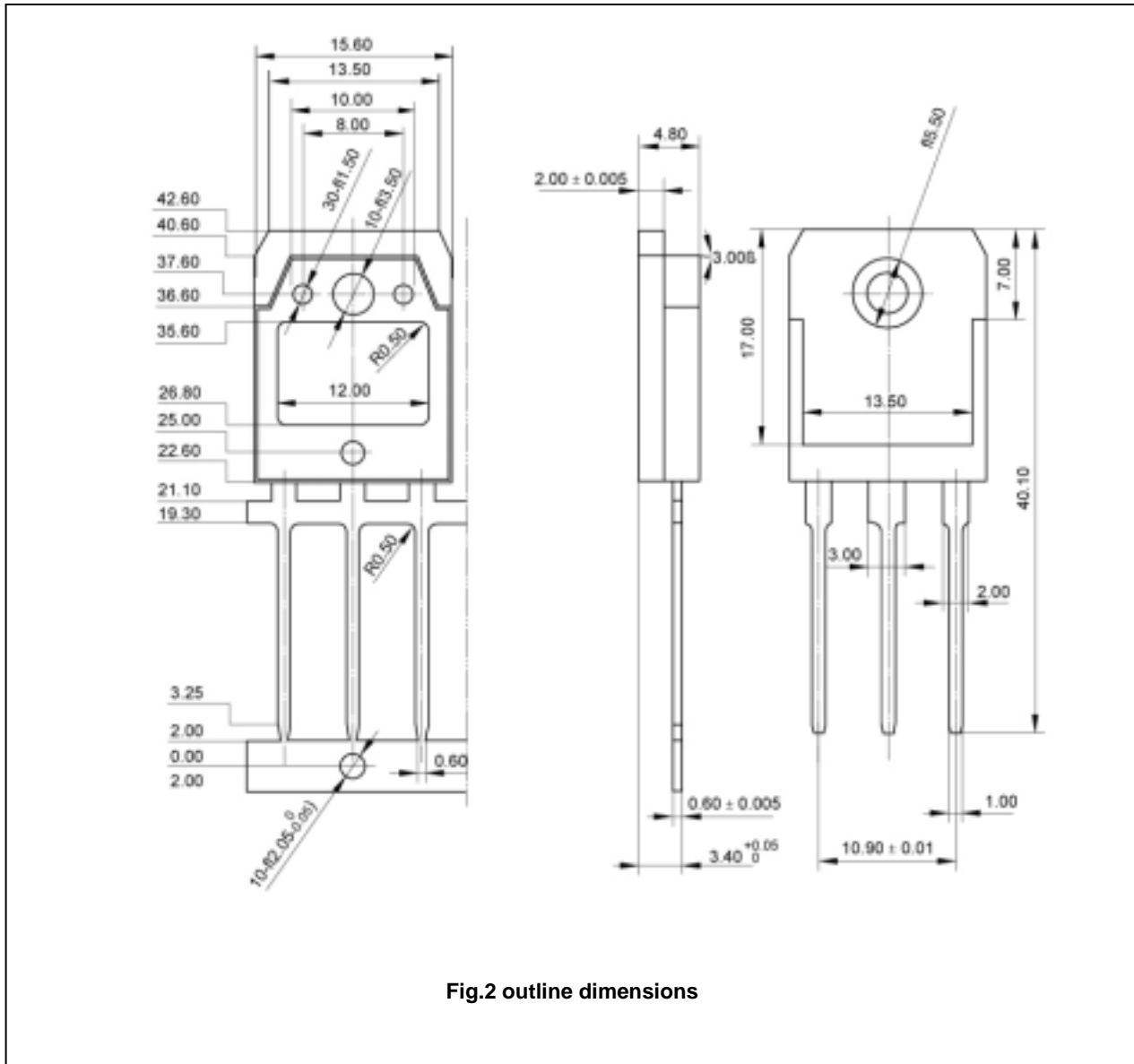


Fig.2 outline dimensions